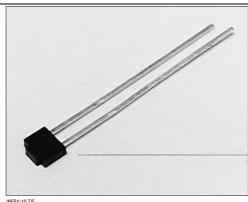
Silicon Phototransistor

FEATURES

- End-looking plastic package
- 135° (nominal) acceptance angle
- Low profile for design flexibility
- · Mechanically and spectrally matched to SEP8507 infrared emitting diode

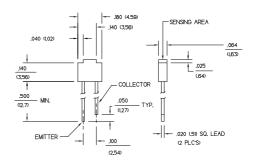


DESCRIPTION

The SDP8407 is an NPN silicon phototransistor molded in an end-looking black plastic package. The chip is positioned to accept radiation from the top of the package. Lead lengths are staggered to provide a simple method of polarity identification.

OUTLINE DIMENSIONS in inches (mm)

3 plc decimals ±0.008(0.20) 2 plc decimals ±0.020(0.51)



DIM_018.ds4

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ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Light Current	l _L				mA	V _{CE} =5 V
SDP8407-001		0.10				H=1 mW/cm ^{2 (1)}
Collector Dark Current	Iceo			100	nA	V _{CE} =10 V, H=0
Collector-Emitter Breakdown Voltage	V _(BR) ceo	30			V	Ic=100 μA
Emitter-Collector Breakdown Voltage	V _{(BR)ECO}	5.0			V	I _E =100 μA
Collector-Emitter Saturation Voltage	VCE(SAT)			0.4	V	lc=10 μA
						H=1 mW/cm ²
Angular Response (2)	Ø		135		degr.	I _F =Constant
Rise And Fall Time	t _r , t _f		15		μs	Vcc=5 V, I _L =1 mA
						R _L =1000 Ω

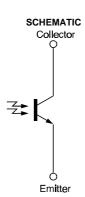
- Notes
 1. The radiation source is an IRED with a peak wavelength of 935 nm.
 2. Angular response is defined as the total included angle between the half sensitivity points.

ABSOLUTE MAXIMUM RATINGS

(25°C Free-Air Temperature unless otherwise noted) Collector-Emitter Voltage 30 V Emitter-Collector Voltage 5 V Power Dissipation 100 mW (1) -40°C to 85C Operating Temperature Range Storage Temperature Range -40°C to 85°C Soldering Temperature (5 sec) 240°C

Notes

1. Derate linearly from 25°C free-air temperature at the rate of 0.66 mW/°C.



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SWITCHING TIME TEST CIRCUIT

GaAs Emitter

H

Emitter

R_L

1000Ω

Po

SWITCHING WAVEFORM

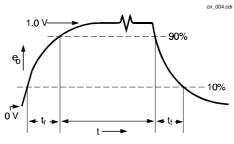


Fig. 1 Responsivity vs Angular Displacement

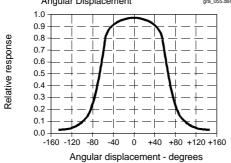


Fig. 2 Collector Current vs

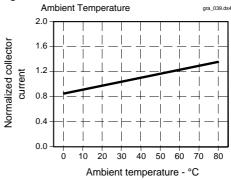


Fig. 3 Dark Current vs

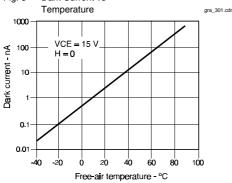
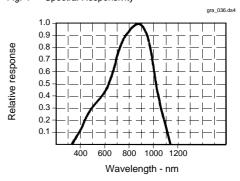


Fig. 4 Spectral Responsivity



All Performance Curves Show Typical Values

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